Shi Pu

List of Publications by Year
in descending order

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23 papers	445 citations	1163117 8 h-index	1372567 10 g-index
23 all docs	23 docs citations	23 times ranked	200 citing authors

#	Article	IF	Citations
1	Aging Mechanisms and Accelerated Lifetime Tests for SiC MOSFETs: An Overview. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2022, 10, 1232-1254.	5.4	35
2	Investigation and On-Board Detection of Gate-Open Failure in SiC MOSFETs. IEEE Transactions on Power Electronics, 2022, 37, 4658-4671.	7.9	5
3	A Comparative Study on Reliability and Ruggedness of Kelvin and Non-Kelvin Packaged SiC Mosfets. IEEE Transactions on Industry Applications, 2022, 58, 3863-3874.	4.9	3
4	A New Complete Condition Monitoring Method for SiC Power MOSFETs. IEEE Transactions on Industrial Electronics, 2021, 68, 1654-1664.	7.9	45
5	Turn-on Delay Based Real-Time Junction Temperature Measurement for SiC MOSFETs With Aging Compensation. IEEE Transactions on Power Electronics, 2021, 36, 1280-1294.	7.9	41
6	A Highly Scalable, Modular Test Bench Architecture for Large-Scale DC Power Cycling of SiC MOSFETs: Towards Data Enabled Reliability. IEEE Power Electronics Magazine, 2021, 8, 39-48.	0.7	13
7	Active Channel Impact on SiC MOSFET Gate Oxide Reliability. , 2021, , .		2
8	Package Degradationâ€™s Impact on SiC MOSFETs Loss: A Comparison of Kelvin and Non-Kelvin Designs. , 2021, , .		3
9	Temperature-Independent Gate-Oxide Degradation Monitoring of SiC MOSFETs Based on Junction Capacitances. IEEE Transactions on Power Electronics, 2021, 36, 8308-8324.	7.9	25
10	An Automated Multi-Device Characterization System for Reliability Assessment of Power Semiconductors. , 2021, , .		1
11	<i>In situ</i> Degradation Monitoring of SiC MOSFET Based on Switching Transient Measurement. IEEE Transactions on Industrial Electronics, 2020, 67, 5092-5100.	7.9	39
12	A System Level Approach for Online Junction Temperature Measurement of SiC MOSFETs Using Turn-On Delay Time. , 2020, , .		3
13	A Practical On-Board SiC MOSFET Condition Monitoring Technique for Aging Detection. IEEE Transactions on Industry Applications, 2020, 56, 2828-2839.	4.9	32
14	On-Board SiC MOSFET Degradation Monitoring Through Readily Available Inverter Current/Voltage Sensors. , 2019, , .		6
15	Design of a High-Performance DC Power Cycling Test Setup for SiC MOSFETs. , 2019, , .		13
16	SiC MOSFET Aging Detection Based on Miller Plateau Voltage Sensing. , 2019, , .		22
17	Degradation Assessment and Precursor Identification for SiC MOSFETs Under High Temp Cycling. IEEE Transactions on Industry Applications, 2019, 55, 2858-2867.	4.9	83
18	Investigation of Agingâ€™s Effect on the Conduction and Switching Loss in SiC MOSFETs. , 2019, , .		10

#	Article	IF	Citations
19	Investigation of Performance Degradation in Enhancement-Mode GaN HEMTs under Accelerated Aging. , 2018, , .		11
20	Thermally Triggered SiC MOSFET Aging Effect on Conducted EMI. , 2018, , .		5
21	Design of a Fast Dynamic On-Resistance Measurement Circuit for GaN Power HEMTs. , 2018, , .		25
22	Real-time degradation monitoring of SiC-MOSFETs through readily available system microcontroller. , 2017, , .		18
23	Investigation of EM radiation changes in SiC based converters throughout device aging. , 2017, , .		5